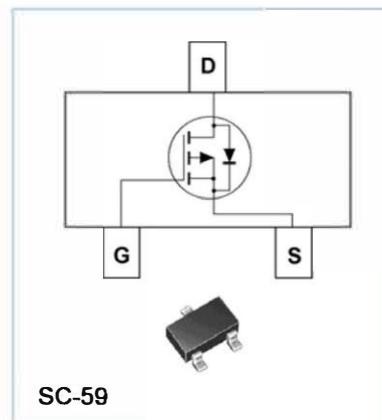


## P-Channel Enhancement Mode MOSFET Feature

- 25V/-4.2A,  $R_{DS(ON)} = 130\text{m}\Omega$ (MAX) @ $V_{GS} = -10\text{V}$ .
- $R_{DS(ON)} = 150\text{m}\Omega$ (MAX) @ $V_{GS} = -4.5\text{V}$ .
- $R_{DS(ON)} = 180\text{m}\Omega$ (MAX) @ $V_{GS} = -2.5\text{V}$ .
- Super High dense cell design for extremely low  $R_{DS(ON)}$
- Reliable and Rugged
- SC-59 for Surface Mount Package
- Marking : AFKA



## Applications

- Power Management
- Portable Equipment and Battery Powered Systems.

T <sub>J</sub>	Maximum Junction Temperature	150	°C
T <sub>TG</sub>	Storage Temperature Range	-55 to 150	

## Absolute Maximum Ratings

T<sub>A</sub>=25°C Unless Otherwise noted

Parameter	Symbol	Limit	Units
Drain-Source Voltage	V <sub>DS</sub>	-25	V
Gate-Source Voltage	V <sub>GS</sub>	±12	V
Drain Current-Continuous	I <sub>D</sub>	-4.2	A

## Electrical Characteristics

T<sub>A</sub>=25°C Unless Otherwise noted

Parameter	Symbol	Test Conditions	Min	Typ.	Max	Units
<b>Off Characteristics</b>						
Drain to Source Breakdown Voltage	BVDSS	V <sub>GS</sub> =0V, I <sub>D</sub> =-250μA	-25	-	-	V
Zero-Gate Voltage Drain Current	IDSS	V <sub>D</sub> =-24V, V <sub>GS</sub> =0V	-	-	-1	μA
Gate Body Leakage Current, Forward	IGSSF	V <sub>GS</sub> =12V, V <sub>D</sub> =0V	-	-	100	nA
Gate Body Leakage Current, Reverse	IGSSR	V <sub>GS</sub> =-12V, V <sub>D</sub> =0V	-	-	-100	nA
<b>On Characteristics</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>GS</sub> = V <sub>D</sub> , I <sub>D</sub> =-250μA	-0.7	-	-1.3	V
Static Drain-source On-Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-4.2A	-	-	130	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-4.0A	-	-	150	mΩ
		V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-1.0A	-	-	180	mΩ
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
Drain-Source Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =-1.0A	-	-	-1.0	V

## Typical Characteristics

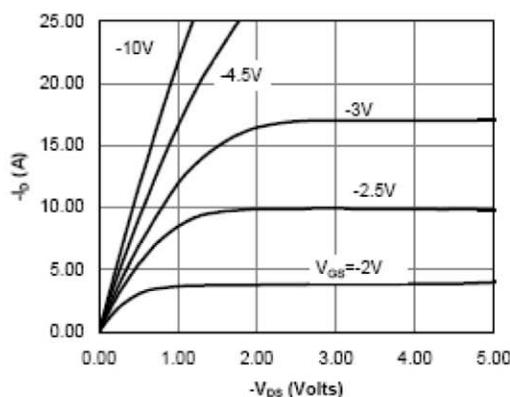


Fig 1: On-Region Characteristics

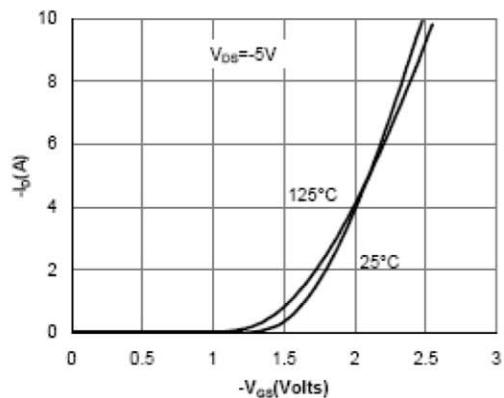


Figure 2: Transfer Characteristics

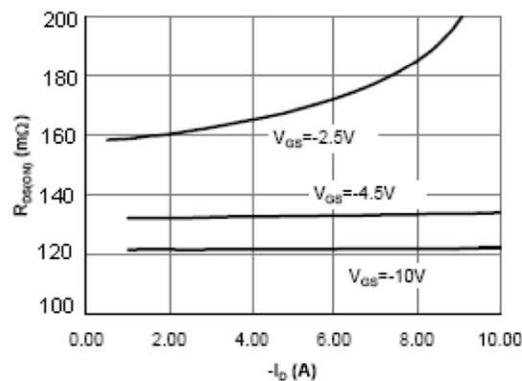


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

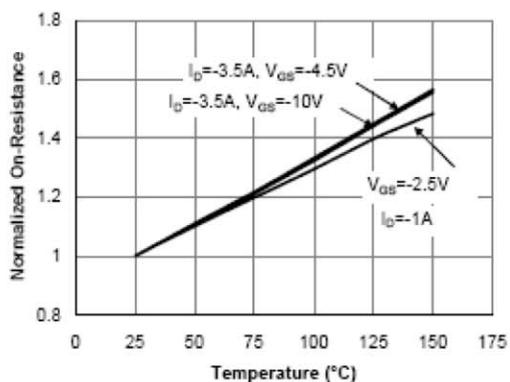


Figure 4: On-Resistance vs. Junction Temperature

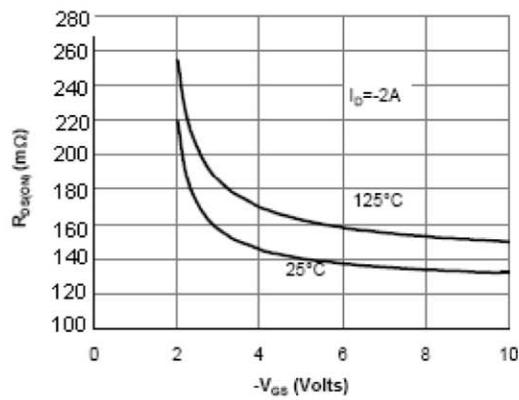


Figure 5: On-Resistance vs. Gate-Source Voltage

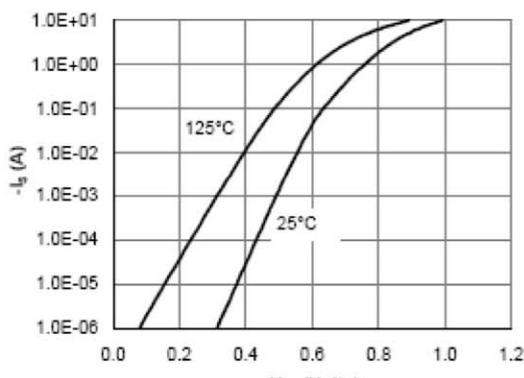


Figure 6: Body-Diode Characteristics

单击下面可查看定价，库存，交付和生命周期等信息

[>>SHIKUES\(时科\)](#)